

DMN65D8L-7 Datasheet



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DiGi Electronics Part Number	DMN65D8L-7-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMN65D8L-7
Description	MOSFET N-CH 60V 310MA SOT23
Detailed Description	N-Channel 60 V 310mA (Ta) 370mW (Ta) Surface Mount SOT-23-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

DMN65D8L-7

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

60 V

Drive Voltage (Max Rds On, Min Rds On):

5V, 10V

Vgs(th) (Max) @ Id:

2V @ 250 μ A

Vgs (Max):

\pm 20V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

SOT-23-3

Base Product Number:

DMN65

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

310mA (Ta)

Rds On (Max) @ Id, Vgs:

30hm @ 115mA, 10V

Gate Charge (Qg) (Max) @ Vgs:

0.87 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

22 pF @ 25 V

Power Dissipation (Max):

370mW (Ta)

Mounting Type:

Surface Mount

Package / Case:

TO-236-3, SC-59, SOT-23-3

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMN65D8L

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
60V	$3\Omega @ V_{GS} = 10V$	310mA
	$4\Omega @ V_{GS} = 5V$	270mA

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

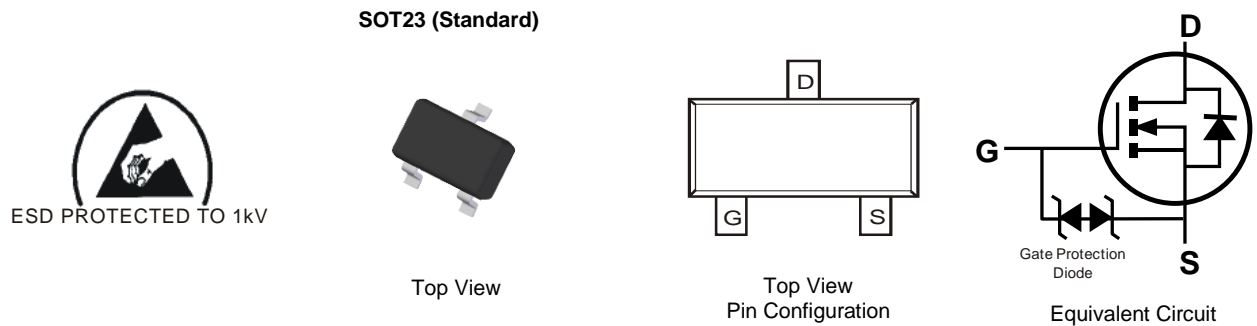
- DC-DC converters
- Power-management functions
- Battery operated systems and solid-state relays
- Drivers: relays, solenoids, lamps, hammers, displays, memories, transistors, etc.

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface-Mount Package
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An automotive-compliant part is available under separate datasheet ([DMN65D8LQ](#))**

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208. Lead Free Plating. Matte Tin Finish Annealed over Alloy 42 Leadframe (e3)
- Terminal Connections: See Diagram
- Weight: 0.008487 grams (Approximate)

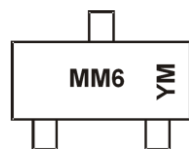


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN65D8L-7	SOT23 (Standard)	3,000	Tape & Reel
DMN65D8L-13	SOT23 (Standard)	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



MM6 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} or \underline{Y} = Year (ex: L = 2024)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2012	...	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	Z	...	L	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



DMN65D8L

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	310 240	mA
Continuous Drain Current (Note 6) V _{GS} = 5V	Steady State	T _A = +25°C T _A = +70°C	I _D	270 210	mA
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	800	mA
Maximum Body Diode Continuous Current (Note 6)			I _S	310	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 6)	P _D	370	mW
	(Note 5)		540	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	348	°C/W
	(Note 5)		241	
Thermal Resistance, Junction to Case	(Note 5)	R _{θJC}	91	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±5	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.2	—	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.9	3	Ω	V _{GS} = 10V, I _D = 0.115A
		—	2.2	4	Ω	V _{GS} = 5V, I _D = 0.115A
Forward Transconductance	g _{FS}	80	290	—	ms	V _{DS} = 10V, I _D = 0.115A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	22	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	3.2	—		
Reverse Transfer Capacitance	C _{RSS}	—	2.0	—		
Gate Resistance	R _g	—	79.9	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	0.87	—	nC	V _{GS} = 10V, V _{DS} = 30V, I _D = 150mA
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	0.43	—		
Gate-Source Charge	Q _{gs}	—	0.11	—		
Gate-Drain Charge	Q _{gd}	—	0.11	—		
Turn-On Delay Time	t _{D(ON)}	—	2.7	—	ns	V _{DD} = 30V, I _D = 0.115A, V _{GEN} = 10V, R _{GEN} = 25Ω
Turn-On Rise Time	t _r	—	2.8	—		
Turn-Off Delay Time	t _{D(OFF)}	—	12.6	—		
Turn-Off Fall Time	t _f	—	7.3	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
 - Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.



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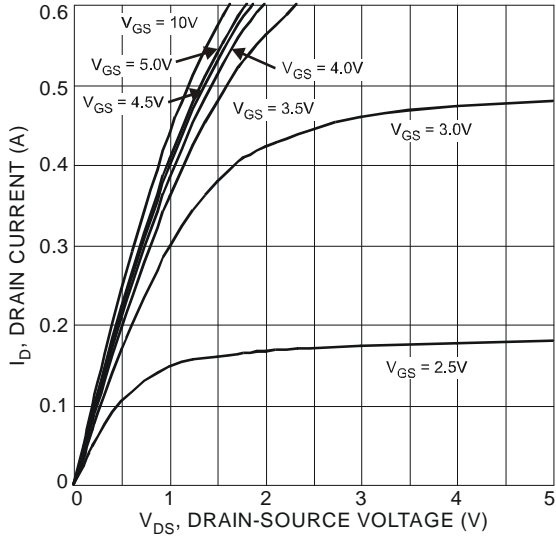


Figure 1. Typical Output Characteristic

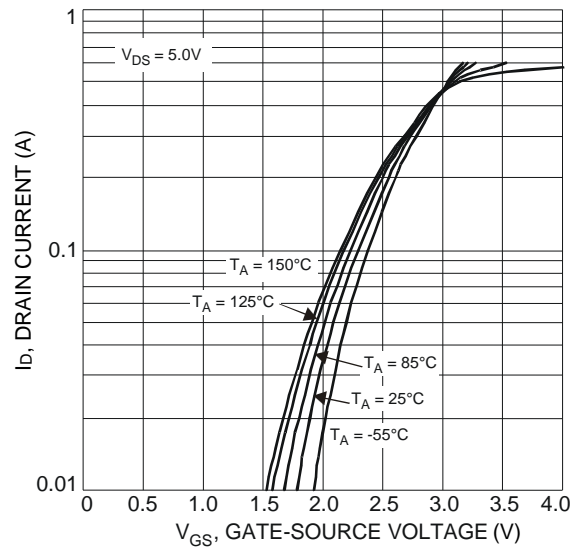


Figure 2. Typical Transfer Characteristics

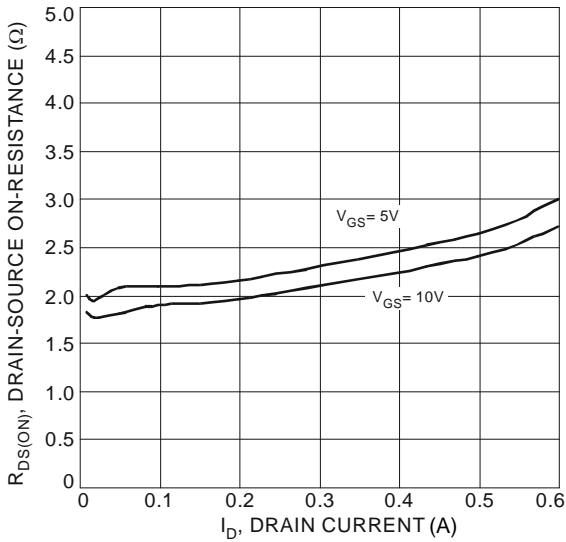


Figure 3. Typical On-Resistance vs. Drain Current and Temperature

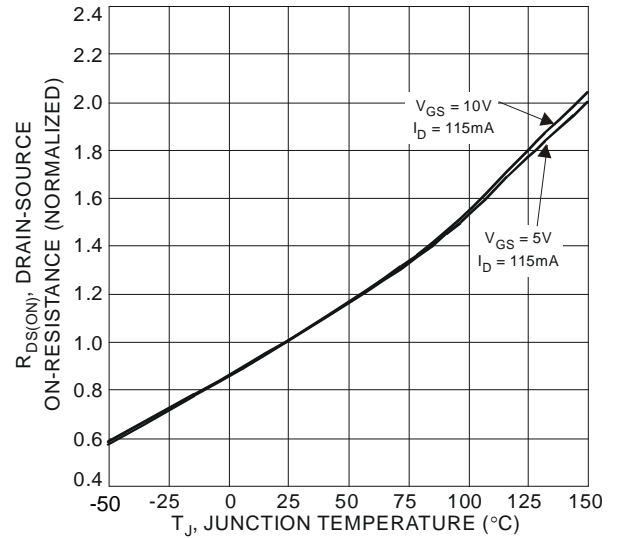


Figure 4. On-Resistance Variation with Temperature

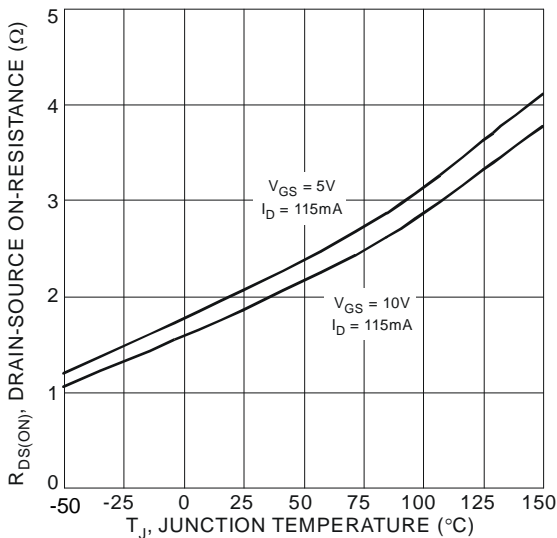


Figure 5. On-Resistance Variation with Temperature

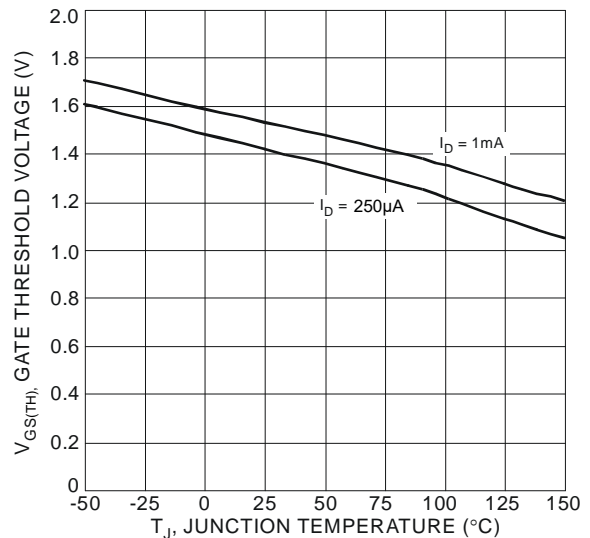


Figure 6. Gate Threshold Variation vs. Junction Temperature



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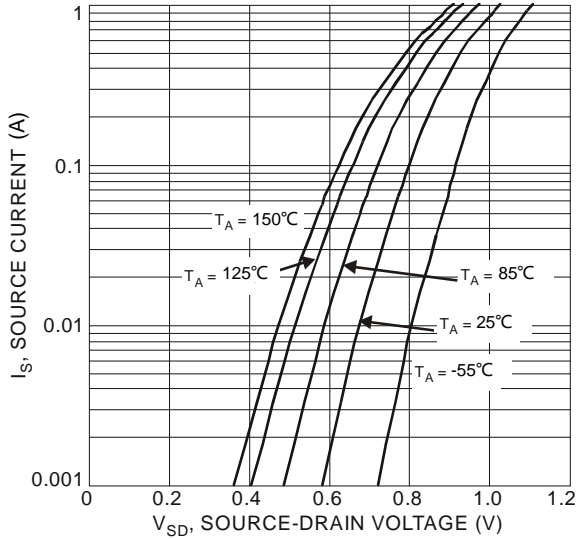


Figure 7. Diode Forward Voltage vs. Current

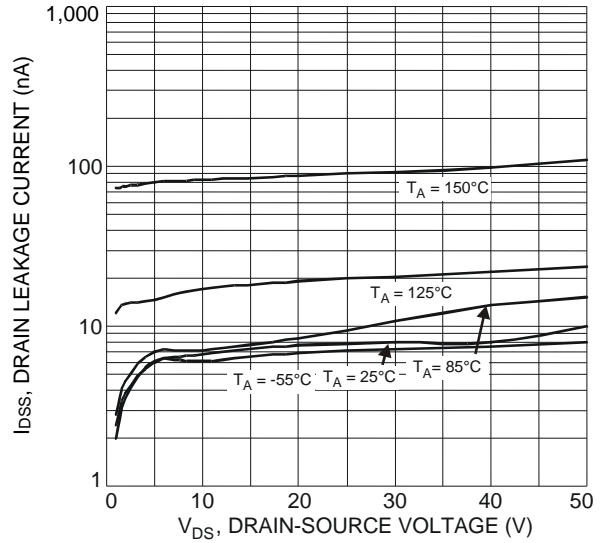


Figure 8. Typical Drain-Source Leakage Current vs. Voltage

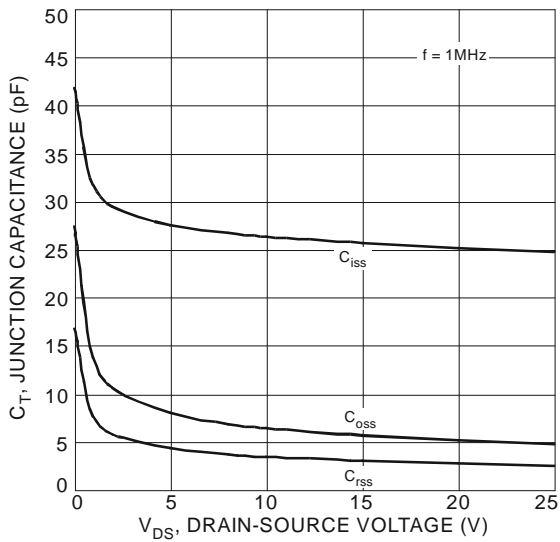
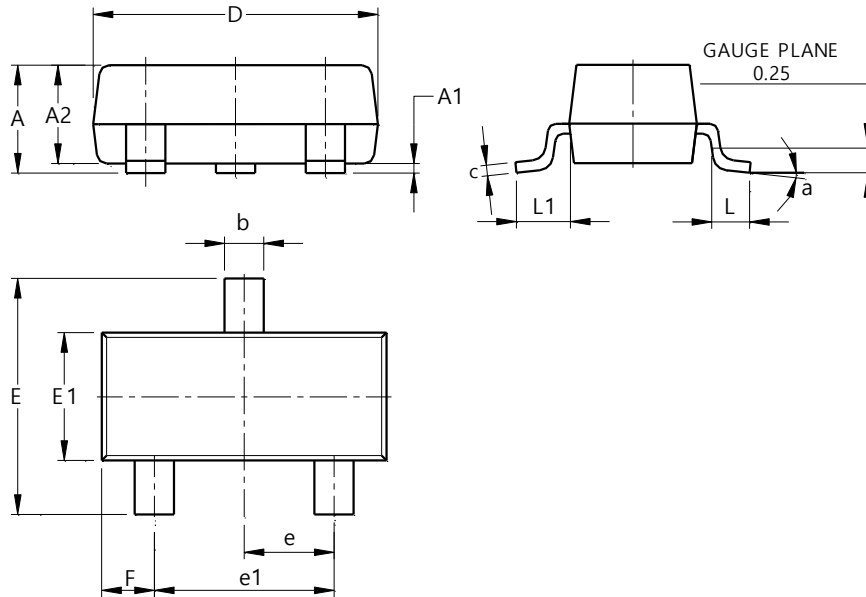


Figure 9. Typical Junction Capacitance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)

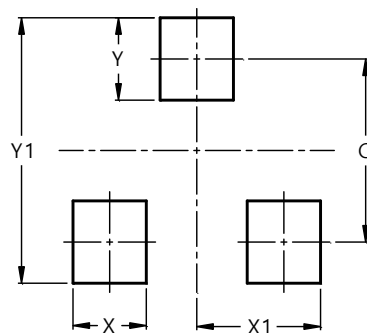


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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